

### Description

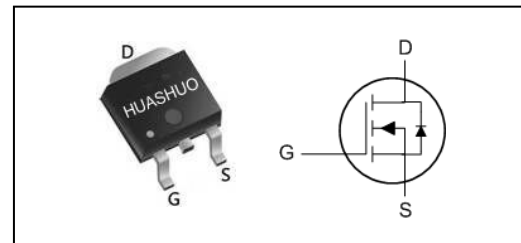
The HSU50N06 is the high cell density trench N-ch MOSFETs, which provide excellent RDSON and gate charge for most of the synchronous buck converter applications. The HSU50N06 meet the RoHS and Green Product requirement, 100% EAS guaranteed with full function reliability approved.

- Super Low Gate Charge
- 100% EAS Guaranteed
- Excellent CdV/dt effect decline
- Green Device Available
- Advanced high cell density Trench technology

### Product Summary

$V_{DS}$	60	V
$R_{DS(ON),max}$	16	m $\Omega$
$I_D$	55	A

### TO252 Pin Configuration



### Absolute Maximum Ratings

Symbol	Parameter	Rating	Units
$V_{DS}$	Drain-Source Voltage	60	V
$V_{GS}$	Gate-Source Voltage	$\pm 20$	V
$I_D@T_C=25^\circ C$	Continuous Drain Current, $V_{GS} @ 10V^1$	55	A
$I_D@T_C=100^\circ C$	Continuous Drain Current, $V_{GS} @ 10V^1$	30	A
$I_{DM}$	Pulsed Drain Current <sup>2</sup>	90	A
EAS	Single Pulse Avalanche Energy <sup>3</sup>	39.2	mJ
$I_{AS}$	Avalanche Current	38	A
$P_D@T_C=25^\circ C$	Total Power Dissipation <sup>4</sup>	45	W
$P_D@T_A=25^\circ C$	Total Power Dissipation <sup>4</sup>	2	W
$T_{STG}$	Storage Temperature Range	-55 to 150	$^\circ C$
$T_J$	Operating Junction Temperature Range	-55 to 150	$^\circ C$

### Thermal Data

Symbol	Parameter	Typ.	Max.	Unit
$R_{\theta JA}$	Thermal Resistance Junction-Ambient <sup>1</sup>	---	62	$^\circ C/W$
$R_{\theta JC}$	Thermal Resistance Junction-Case <sup>1</sup>	---	2.8	$^\circ C/W$



**Electrical Characteristics (T<sub>J</sub>=25 °C, unless otherwise noted)**

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
BV <sub>DSS</sub>	Drain-Source Breakdown Voltage	V <sub>GS</sub> =0V, I <sub>D</sub> =250uA	60	---	---	V
ΔBV <sub>DSS</sub> /ΔT <sub>J</sub>	BV <sub>DSS</sub> Temperature Coefficient	Reference to 25°C, I <sub>D</sub> =1mA	---	0.057	---	V/°C
R <sub>DS(ON)</sub>	Static Drain-Source On-Resistance <sup>2</sup>	V <sub>GS</sub> =10V, I <sub>D</sub> =20A	---	11	16	mΩ
		V <sub>GS</sub> =4.5V, I <sub>D</sub> =10A	---	16	20	
V <sub>GS(th)</sub>	Gate Threshold Voltage	V <sub>GS</sub> =V <sub>DS</sub> , I <sub>D</sub> =250uA	1.2	1.8	2.5	V
ΔV <sub>GS(th)</sub>	V <sub>GS(th)</sub> Temperature Coefficient		---	-5.68	---	mV/°C
I <sub>DSS</sub>	Drain-Source Leakage Current	V <sub>DS</sub> =48V, V <sub>GS</sub> =0V, T <sub>J</sub> =25°C	---	---	1	uA
		V <sub>DS</sub> =48V, V <sub>GS</sub> =0V, T <sub>J</sub> =55°C	---	---	5	
I <sub>GSS</sub>	Gate-Source Leakage Current	V <sub>GS</sub> =±20V, V <sub>DS</sub> =0V	---	---	±100	nA
g <sub>fs</sub>	Forward Transconductance	V <sub>DS</sub> =5V, I <sub>D</sub> =15A	---	45	---	S
R <sub>g</sub>	Gate Resistance	V <sub>DS</sub> =0V, V <sub>GS</sub> =0V, f=1MHz	---	1.7	---	Ω
Q <sub>g</sub>	Total Gate Charge (4.5V)	V <sub>DS</sub> =48V, V <sub>GS</sub> =4.5V, I <sub>D</sub> =15A	---	23	---	nC
Q <sub>gs</sub>	Gate-Source Charge		---	7.1	---	
Q <sub>gd</sub>	Gate-Drain Charge		---	7.6	---	
T <sub>d(on)</sub>	Turn-On Delay Time	V <sub>DD</sub> =30V, V <sub>GS</sub> =10V, R <sub>G</sub> =3.3Ω, I <sub>D</sub> =15A	---	7.2	---	ns
T <sub>r</sub>	Rise Time		---	50	---	
T <sub>d(off)</sub>	Turn-Off Delay Time		---	36.4	---	
T <sub>f</sub>	Fall Time		---	7.6	---	
C <sub>iss</sub>	Input Capacitance	V <sub>DS</sub> =15V, V <sub>GS</sub> =0V, f=1MHz	---	2823	---	pF
C <sub>oss</sub>	Output Capacitance		---	155	---	
C <sub>rss</sub>	Reverse Transfer Capacitance		---	107	---	

**Diode Characteristics**

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
I <sub>S</sub>	Continuous Source Current <sup>1,5</sup>	V <sub>G</sub> =V <sub>D</sub> =0V, Force Current	---	---	55	A
I <sub>SM</sub>	Pulsed Source Current <sup>2,5</sup>		---	---	90	A
V <sub>SD</sub>	Diode Forward Voltage <sup>2</sup>	V <sub>GS</sub> =0V, I <sub>S</sub> =A, T <sub>J</sub> =25°C	---	---	1	V
t <sub>rr</sub>	Reverse Recovery Time	I <sub>F</sub> =15A, di/dt=100A/μs,	---	16.3	---	nS
Q <sub>rr</sub>	Reverse Recovery Charge	T <sub>J</sub> =25°C	---	11	---	nC

Note :

- 1.The data tested by surface mounted on a 1 inch<sup>2</sup> FR-4 board with 2OZ copper.
- 2.The data tested by pulsed, pulse width ≤ 300us, duty cycle ≤ 2%
- 3.The EAS data shows Max. rating. The test condition is V<sub>DD</sub>=25V, V<sub>GS</sub>=10V, L=0.1mH, I<sub>AS</sub>=38A
- 4.The power dissipation is limited by 150°C junction temperature
- 5.The data is theoretically the same as I<sub>D</sub> and I<sub>DM</sub>, in real applications, should be limited by total power dissipation.



### Typical Characteristics

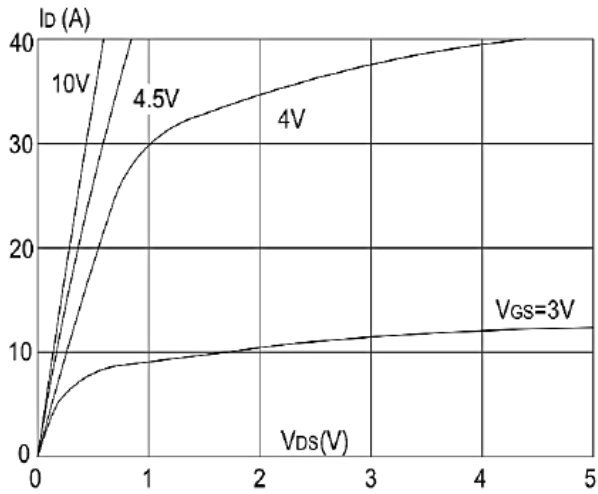


Figure 1: Output Characteristics

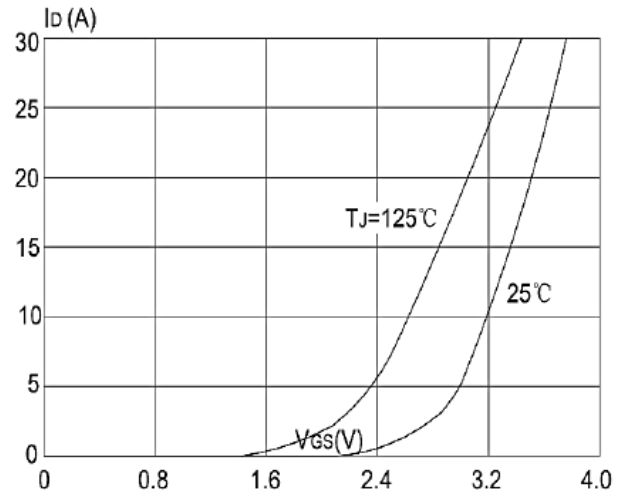


Figure 2: Typical Transfer Characteristics

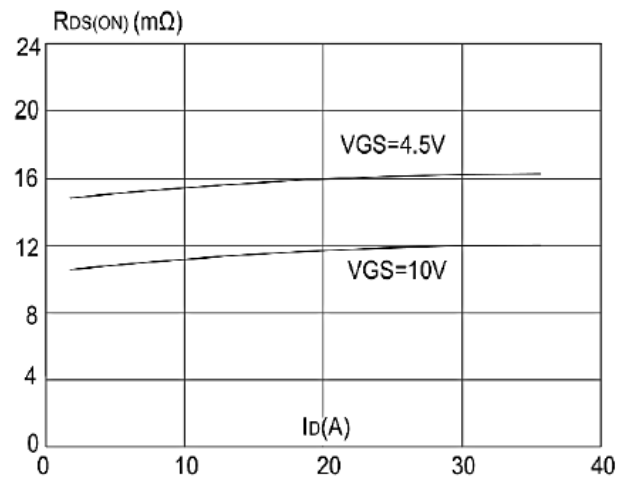


Figure 3: On-resistance vs. Drain Current

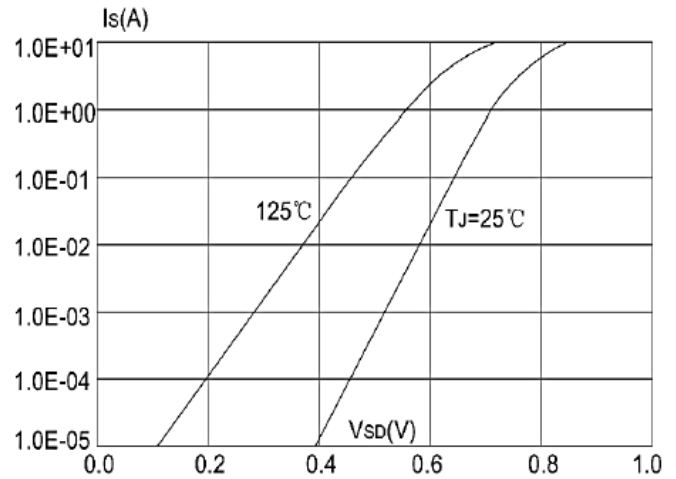


Figure 4: Body Diode Characteristics

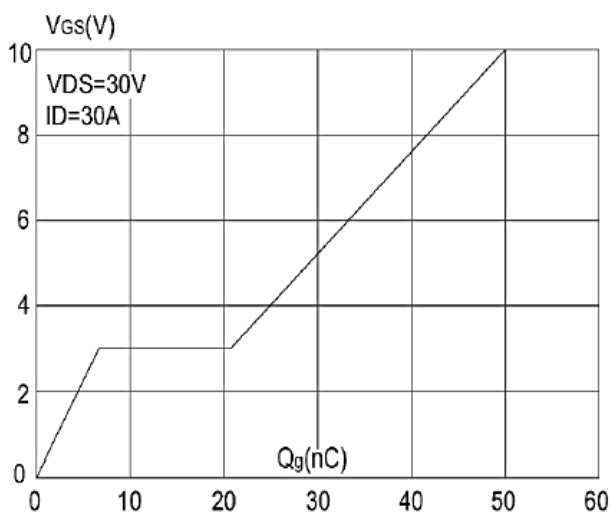


Figure 5: Gate Charge Characteristics

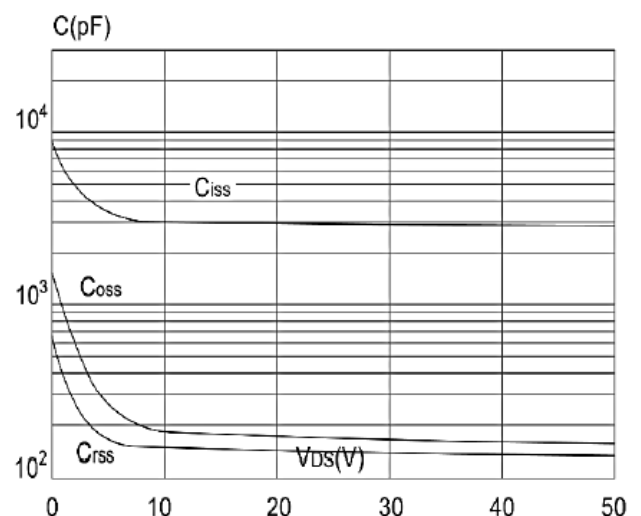
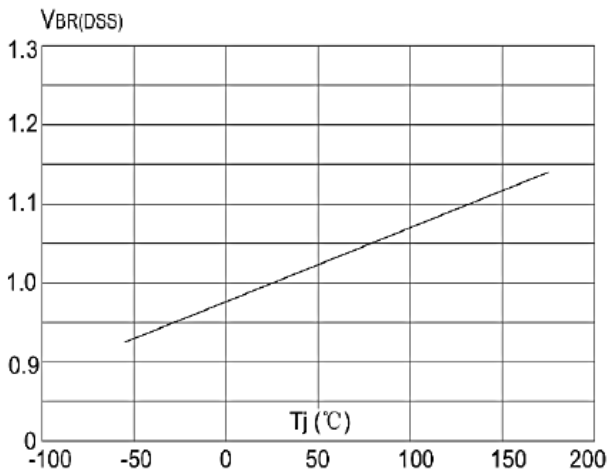
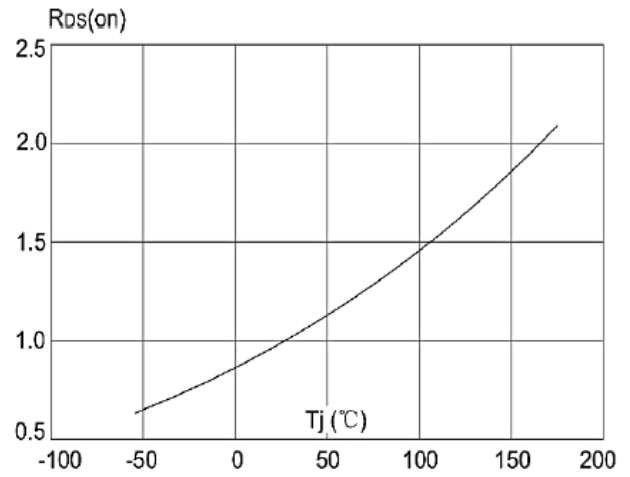


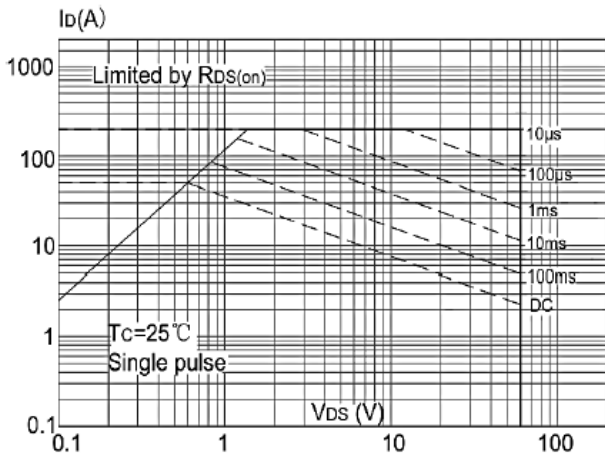
Figure 6: Capacitance Characteristics



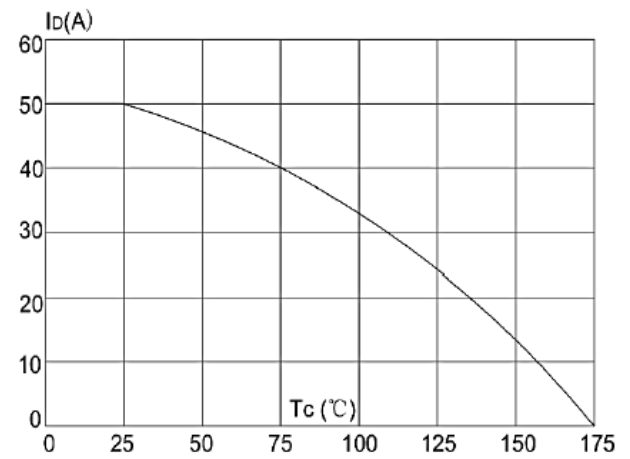
**Figure 7: Normalized Breakdown Voltage vs Junction Temperature**



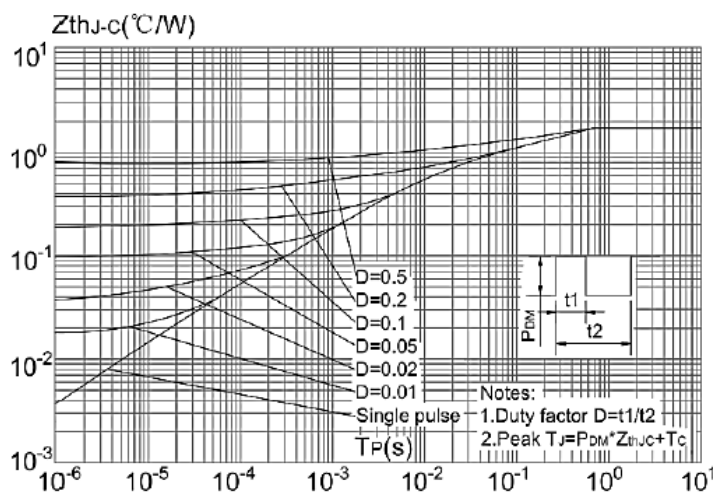
**Figure 8: Normalized on Resistance vs. Junction Temperature**



**Figure 9: Maximum Safe Operating Area**



**Figure 10: Maximum Continuous Drain Current vs. Ambient Temperature**

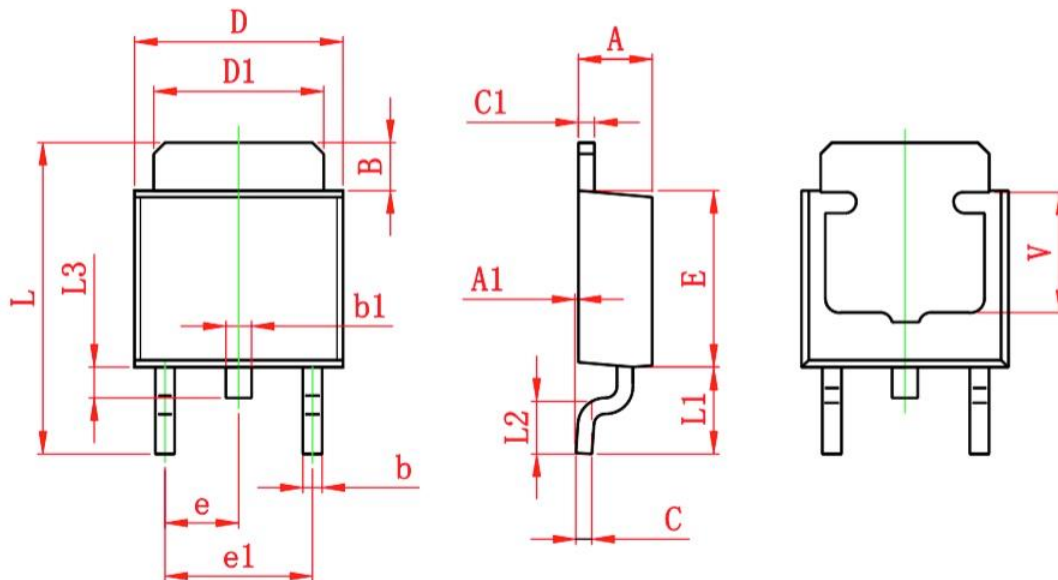


**Figure.11: Maximum Effective Transient Thermal Impedance, Junction-to-Ambien**



## Ordering Information

Part Number	Package code	Packaging
HSU50N06	TO252-2	2500/Tape&Reel



Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min.	Max.	Min.	Max.
A	2.200	2.400	0.087	0.094
A1	0.000	0.127	0.000	0.005
B	1.350	1.650	0.053	0.065
b	0.500	0.700	0.020	0.028
b1	0.700	0.900	0.028	0.035
c	0.430	0.580	0.017	0.023
c1	0.430	0.580	0.017	0.023
D	6.350	6.650	0.250	0.262
D1	5.200	5.400	0.205	0.213
E	5.400	5.700	0.213	0.224
e	2.300 TYP.		0.091 TYP.	
e1	4.500	4.700	0.177	0.185
L	9.500	9.900	0.374	0.390
L1	2.550	2.900	0.100	0.114
L2	1.400	1.780	0.055	0.070
L3	0.600	0.900	0.024	0.035
V	3.800 REF.		0.150 REF.	